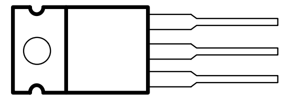
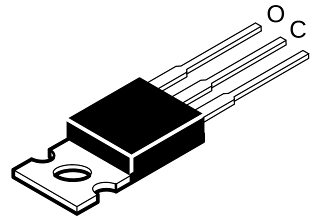
- **3-Terminal Regulators**
- **Output Current up to 1.5 A**
- **Internal Thermal-Overload Protection**
- **High Power-Dissipation Capability**
- **Internal Short-Circuit Current Limiting**
- **Output Transistor Safe-Area Compensation**
- **Direct Replacements for Fairchild µA7800 Series**

**KC PACKAGE
(TOP VIEW)**

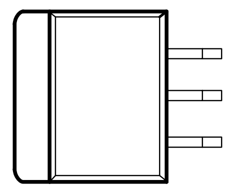


The COMMON terminal is in electrical contact with the mounting base.

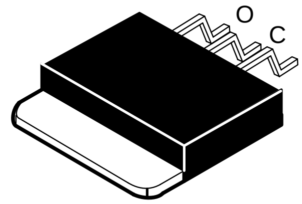
TO-220AB



**KTE PACKAGE
(TOP VIEW)**



The COMMON terminal is in electrical contact with the mounting base.



description

This series of fixed-voltage monolithic integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. Each of these regulators can deliver up to 1.5 A of output current. The internal current-limiting and thermal-shutdown features of these regulators essentially make them immune to overload. In addition to use as fixed-voltage regulators, these devices can be used with external components to obtain adjustable output voltages and currents, and also can be used as the power-pass element in precision regulators.

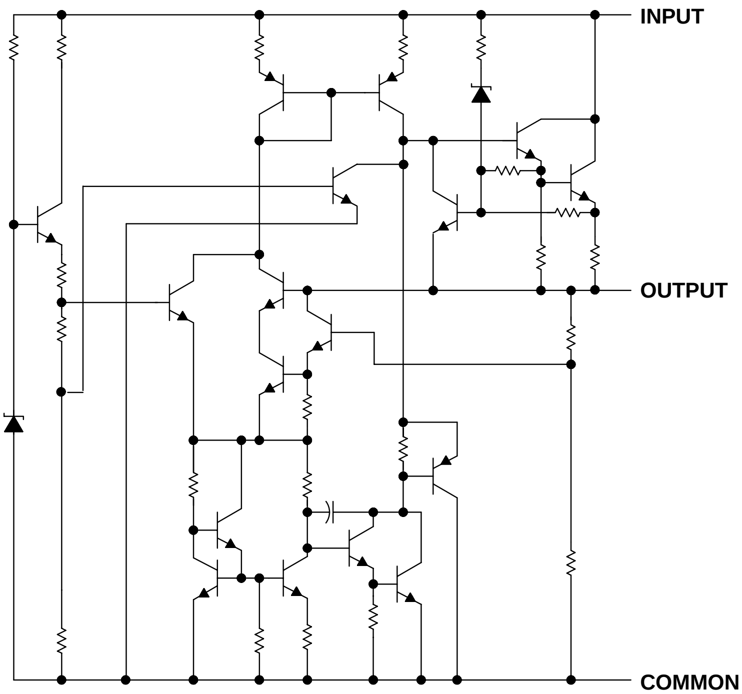
The µA7800C series is characterized for operation over the virtual junction temperature range of 0°C to 125°C.

AVAILABLE OPTIONS

T_J	$V_{O(NOM)}$ (V)	PACKAGED DEVICES	
		PLASTIC FLANGE MOUNT (KC)	HEAT-SINK MOUNTED (KTE)
0°C to 125°C	5	µA7805CKC	µA7805CKTE
	8	µA7808CKC	µA7808CKTE
	10	µA7810CKC	µA7810CKTE
	12	µA7812CKC	µA7812CKTE
	15	µA7815CKC	µA7815CKTE
	24	µA7824CKC	µA7824CKTE

The KTE package is only available taped and reeled. Add the suffix R to the device type (e.g., µA7805CKTER).

schematic



absolute maximum ratings over virtual junction temperature range (unless otherwise noted)†

Input voltage, V_I: µA7824C . . . . 40 V
All others . . . . 35 V
Package thermal impedance, θ_{JA} (see Notes 1 and 2): KC package . . . . 22°C/W
(see Notes 1 and 3): KTE package . . . . 23°C/W
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . 260°C
Virtual junction temperature range, T_J . . . . 0°C to 150°C
Storage temperature range, T_{stg} . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) – T_A)/\theta_{JA}$. Selecting the maximum of 150°C can impact reliability.
2. The package thermal impedance is calculated in accordance with JESD 51-7.
3. The package thermal impedance is calculated in accordance with JESD 51-5.

recommended operating conditions

			MIN	MAX	UNIT
V_I	Input voltage	µA7805C	7	25	V
		µA7808C	10.5	25	
		µA7810C	12.5	28	
		µA7812C	14.5	30	
		µA7815C	17.5	30	
		µA7824C	27	38	
I_O	Output current			1.5	A
T_J	Operating virtual junction temperature	µA7800C series	0	125	°C

electrical characteristics at specified virtual junction temperature, V_I = 10 V, I_O = 500 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_J†	µA7805C MIN	µA7805C TYP	µA7805C MAX	UNIT
Output voltage	I_O = 5 mA to 1 A, V_I = 7 V to 20 V, $P_D \le$ 15 W	25°C	4.8	5	5.2	V
		0°C to 125°C	4.75		5.25	
Input voltage regulation	V_I = 7 V to 25 V	25°C		3	100	mV
	V_I = 8 V to 12 V			1	50	
Ripple rejection	V_I = 8 V to 18 V, f = 120 Hz	0°C to 125°C	62	78		dB
Output voltage regulation	I_O = 5 mA to 1.5 A	25°C		15	100	mV
	I_O = 250 mA to 750 mA			5	50	
Output resistance	f = 1 kHz	0°C to 125°C		0.017		Ω
Temperature coefficient of output voltage	I_O = 5 mA	0°C to 125°C		–1.1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		40		µV
Dropout voltage	I_O = 1 A	25°C		2		V
Bias current		25°C		4.2	8	mA
Bias current change	V_I = 7 V to 25 V	0°C to 125°C			1.3	mA
	I_O = 5 mA to 1 A				0.5	
Short-circuit output current		25°C		750		mA
Peak output current		25°C		2.2		A

† Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 500 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_J†	µA7808C MIN	µA7808C TYP	µA7808C MAX	UNIT
Output voltage	I_O = 5 mA to 1 A, V_I = 10.5 V to 23 V, $P_D \le$ 15 W	25°C	7.7	8	8.3	V
		0°C to 125°C	7.6		8.4	
Input voltage regulation	V_I = 10.5 V to 25 V	25°C		6	160	mV
	V_I = 11 V to 17 V			2	80	
Ripple rejection	V_I = 11.5 V to 21.5 V, f = 120 Hz	0°C to 125°C	55	72		dB
Output voltage regulation	I_O = 5 mA to 1.5 A	25°C		12	160	mV
	I_O = 250 mA to 750 mA			4	80	
Output resistance	f = 1 kHz	0°C to 125°C		0.016		Ω
Temperature coefficient of output voltage	I_O = 5 mA	0°C to 125°C		–0.8		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		52		µV
Dropout voltage	I_O = 1 A	25°C		2		V
Bias current		25°C		4.3	8	mA
Bias current change	V_I = 10.5 V to 25 V	0°C to 125°C			1	mA
	I_O = 5 mA to 1 A				0.5	
Short-circuit output current		25°C		450		mA
Peak output current		25°C		2.2		A

† Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 17 V, I_O = 500 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS		T_J†	μA7810C MIN	μA7810C TYP	μA7810C MAX	UNIT
Output voltage	I_O = 5 mA to 1 A, P_D ≤ 15 W	V_I = 12.5 V to 25 V,	25°C	9.6	10	10.4	V
			0°C to 125°C	9.5	10	10.5	
Input voltage regulation	V_I = 12.5 V to 28 V		25°C		7	200	mV
	V_I = 14 V to 20 V				2	100	
Ripple rejection	V_I = 13 V to 23 V,	f = 120 Hz	0°C to 125°C	55	71		dB
Output voltage regulation	I_O = 5 mA to 1.5 A		25°C		12	200	mV
	I_O = 250 mA to 750 mA				4	100	
Output resistance	f = 1 kHz		0°C to 125°C		0.018		Ω
Temperature coefficient of output voltage	I_O = 5 mA		0°C to 125°C		–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz		25°C		70		μV
Dropout voltage	I_O = 1 A		25°C		2		V
Bias current			25°C		4.3	8	mA
Bias current change	V_I = 12.5 V to 28 V		0°C to 125°C			1	mA
	I_O = 5 mA to 1 A					0.5	
Short-circuit output current			25°C		400		mA
Peak output current			25°C		2.2		A

† Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 19 V, I_O = 500 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS		T_J†	μA7812C MIN	μA7812C TYP	μA7812C MAX	UNIT
Output voltage	I_O = 5 mA to 1 A, P_D ≤ 15 W	V_I = 14.5 V to 27 V,	25°C	11.5	12	12.5	V
			0°C to 125°C	11.4		12.6	
Input voltage regulation	V_I = 14.5 V to 30 V		25°C		10	240	mV
	V_I = 16 V to 22 V				3	120	
Ripple rejection	V_I = 15 V to 25 V,	f = 120 Hz	0°C to 125°C	55	71		dB
Output voltage regulation	I_O = 5 mA to 1.5 A		25°C		12	240	mV
	I_O = 250 mA to 750 mA				4	120	
Output resistance	f = 1 kHz		0°C to 125°C		0.018		Ω
Temperature coefficient of output voltage	I_O = 5 mA		0°C to 125°C		–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz		25°C		75		μV
Dropout voltage	I_O = 1 A		25°C		2		V
Bias current			25°C		4.3	8	mA
Bias current change	V_I = 14.5 V to 30 V		0°C to 125°C			1	mA
	I_O = 5 mA to 1 A					0.5	
Short-circuit output current			25°C		350		mA
Peak output current			25°C		2.2		A

† Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 23 V, I_O = 500 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS		T_J†	µA7815C MIN	µA7815C TYP	µA7815C MAX	UNIT
Output voltage	I_O = 5 mA to 1 A, $P_D \leq$ 15 W	V_I = 17.5 V to 30 V,	25°C	14.4	15	15.6	V
			0°C to 125°C	14.25		15.75	
Input voltage regulation	V_I = 17.5 V to 30 V		25°C		11	300	mV
	V_I = 20 V to 26 V				3	150	
Ripple rejection	V_I = 18.5 V to 28.5 V,	f = 120 Hz	0°C to 125°C	54	70		dB
Output voltage regulation	I_O = 5 mA to 1.5 A		25°C		12	300	mV
	I_O = 250 mA to 750 mA				4	150	
Output resistance	f = 1 kHz		0°C to 125°C		0.019		Ω
Temperature coefficient of output voltage	I_O = 5 mA		0°C to 125°C		–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz		25°C		90		µV
Dropout voltage	I_O = 1 A		25°C		2		V
Bias current			25°C		4.4	8	mA
Bias current change	V_I = 17.5 V to 30 V		0°C to 125°C			1	mA
	I_O = 5 mA to 1 A					0.5	
Short-circuit output current			25°C		230		mA
Peak output current			25°C		2.1		A

† Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 33 V, I_O = 500 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS		T_J†	µA7824C MIN	µA7824C TYP	µA7824C MAX	UNIT
Output voltage	I_O = 5 mA to 1 A, $P_D \leq$ 15 W	V_I = 27 V to 38 V,	25°C	23	24	25	V
			0°C to 125°C	22.8		25.2	
Input voltage regulation	V_I = 27 V to 38 V		25°C		18	480	mV
	V_I = 30 V to 36 V				6	240	
Ripple rejection	V_I = 28 V to 38 V,	f = 120 Hz	0°C to 125°C	50	66		dB
Output voltage regulation	I_O = 5 mA to 1.5 A		25°C		12	480	mV
	I_O = 250 mA to 750 mA				4	240	
Output resistance	f = 1 kHz		0°C to 125°C		0.028		Ω
Temperature coefficient of output voltage	I_O = 5 mA		0°C to 125°C		–1.5		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz		25°C		170		µV
Dropout voltage	I_O = 1 A		25°C		2		V
Bias current			25°C		4.6	8	mA
Bias current change	V_I = 27 V to 38 V		0°C to 125°C			1	mA
	I_O = 5 mA to 1 A					0.5	
Short-circuit output current			25°C		150		mA
Peak output current			25°C		2.1		A

† Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

APPLICATION INFORMATION

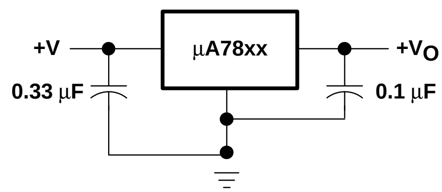


Figure 1. Fixed-Output Regulator

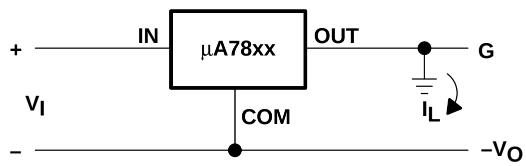
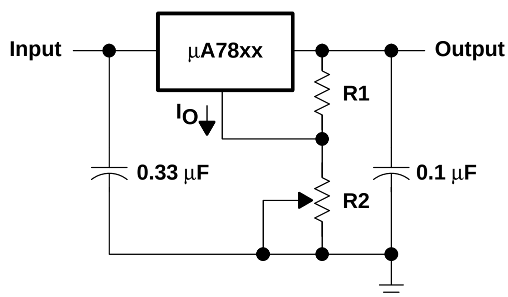


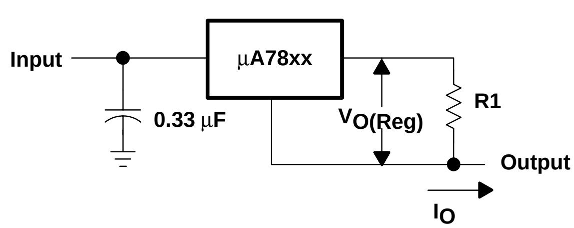
Figure 2. Positive Regulator in Negative Configuration (V_I Must Float)



NOTE A: The following formula is used when V_{XX} is the nominal output voltage (output to common) of the fixed regulator:

$$V_O = V_{xx} + \left(\frac{V_{xx}}{R1} + I_Q\right)R2$$

Figure 3. Adjustable-Output Regulator



$I_O = (V_O/R1) + I_O$ Bias Current

Figure 4. Current Regulator

APPLICATION INFORMATION

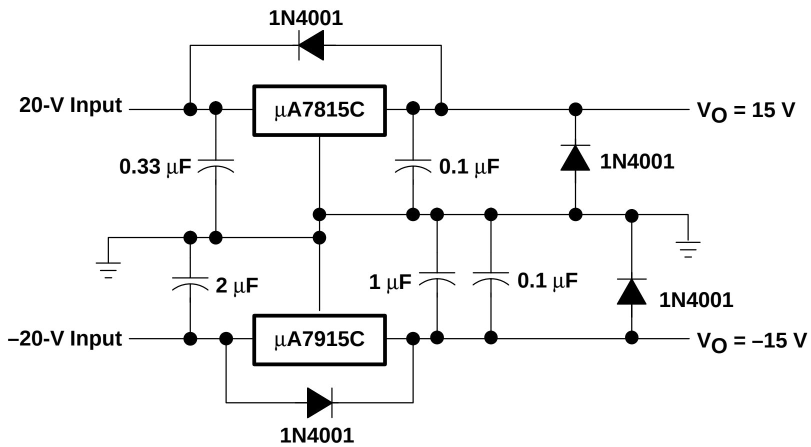


Figure 5. Regulated Dual Supply

operation with a load common to a voltage of opposite polarity

In many cases, a regulator powers a load that is not connected to ground but, instead, is connected to a voltage source of opposite polarity (e.g., operational amplifiers, level-shifting circuits, etc.). In these cases, a clamp diode should be connected to the regulator output as shown in Figure 6. This protects the regulator from output polarity reversals during startup and short-circuit operation.

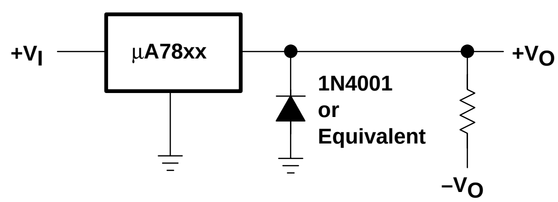


Figure 6. Output Polarity-Reversal-Protection Circuit

reverse-bias protection

Occasionally, the input voltage to the regulator can collapse faster than the output voltage. This can occur, for example, when the input supply is crowbarred during an output overvoltage condition. If the output voltage is greater than approximately 7 V, the emitter-base junction of the series-pass element (internal or external) could break down and be damaged. To prevent this, a diode shunt can be used as shown in Figure 7.

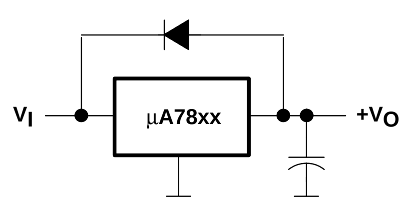


Figure 7. Reverse-Bias-Protection Circuit

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